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(21) International Application Number: PCT/US99/18660 (22) International Filing Date: 17 August 1999 (17.08.99) (30) Priority Data: 09/303,168 30 April 1999 (30.04.99) US (71) Applicant: 3M INNOVATIVE PROPERTIES COMPANY [US/US]; 3M Center, P.O. Box 33427, Saint Paul, MN 55133-3427 (US). (72) Inventor: LU, David, D.; P.O. Box 33427, Saint Paul, MN 55133-3427 (US). (74) Agents: FONSECA, Darla, P. et al.; 3M Innovative Properties Company, Office of Intellectual Property Counsel, P.O. Box 33427, Saint Paul, MN 55133-3427 (US).		(81) Designated States: AE, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, CA, CH, CN, CR, CU, CZ, DE, DK, DM, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MD, MG, MK, MN, MW, MX, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, UA, UG, UZ, VN, YU, ZA, ZW, ARIPO patent (GH, GM, KE, LS, MW, SD, SL, SZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG). Published <i>With international search report.</i>	
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(54) Title: A METHOD FOR MAKING FLEXIBLE CIRCUITS			
(57) Abstract			
<p>A process for making flexible circuits wherein the etching of a polymeric film is accomplished by dissolving portions thereof with concentrated aqueous base using a UV-curable 100 % active liquid photoresist as a mask, comprising the steps of laminating the resist on a polymeric film, exposing a pattern into the resist, developing the resist with a dilute aqueous solution until desired image is obtained, etching portions of the polymeric film not covered by the crosslinked resist with a concentrated base at a temperature of from 50 °C to 120 °C, and then stripping the resist off the polymeric film.</p>			
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